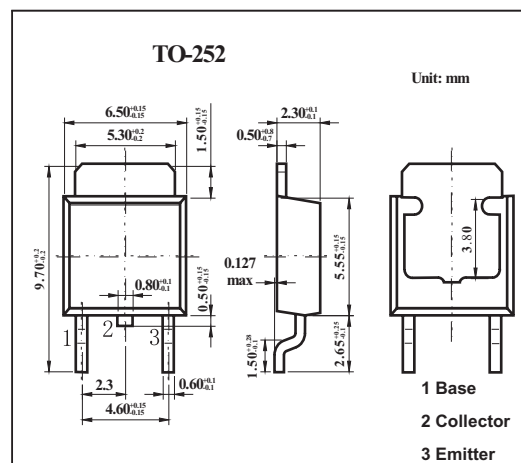


High-Current Switching Applications

2SB1216

■ Features

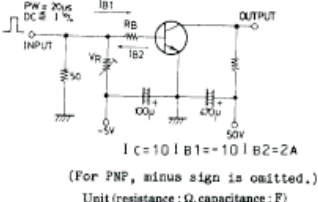
- Low collector-to-emitter saturation voltage.
- Good linearity of h_{FE} .
- High f_T .
- Fast switching time.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-120	V
Collector-emitter voltage	V_{CEO}	-100	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-4	A
Collector current (pulse)	I_{CP}	-8	A
Collector dissipation	P_C	1	W
$T_C = 25^\circ\text{C}$		20	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	ICBO	V _{CB} = -100V, I _E = 0			-1	μA
Emitter cutoff current	IEBO	V _{EB} = -4V, I _C = 0			-1	μA
DC current Gain	h _{FE}	V _{CE} = -5V, I _C = -0.5A	70		400	
		V _{CE} = -5V, I _C = -3A	40			
Gain bandwidth product	f _T	V _{CE} = -10V, I _C = -0.5A		130		MHz
Output capacitance	C _{ob}	V _{CB} = -10V, f = 1MHz		65		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -2A, I _B = -0.2A		-200	-500	mV
Base-to-emitter saturation voltage	V _{BE(sat)}	I _C = -2A, I _B = -0.2A		-0.9	-1.2	V
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-120			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-100			V
Emitter-to-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-6			V
Turn-on time	t _{on}	 <p>IC = 10 I_{B1} = 10 I_{B2} = 2A (For PNP, minus sign is omitted.) Unit (resistance : Ω, capacitance : F)</p>		100		ns
Storage time	t _{stg}			800		ns
Fall time	t _f			50		ns

■ h_{FE} Classification

Rank	Q	R	S	T
h _{FE}	70~140	100~200	140~280	200~400